

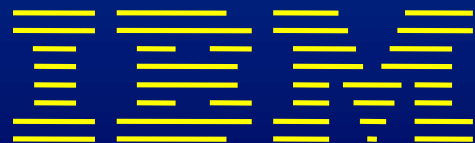
# Probing Lead Free Solder Bumps in Final Wafer Test

By

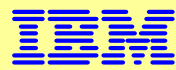
**Sam McKnight**

Southwest Test Workshop

June 2002



Microelectronics



# Outline

**Why lead free ?**

**Background Info**

**Focus areas**

**Setup**

**Lead/Tin and Tin “Rich” results**

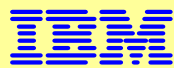
**Summary**

**Acknowledgements**



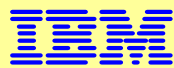
## Why Lead Free?

- Increasing use of integrated circuits and shortened product life cycles prompted a world wide environmental concern regarding the disposal of electronic components.
- Lead countries with environmental initiatives are Japan, Europe and the US
- All levels of packaging including the interconnect to the integrated circuit are being addressed.
- This presentation focuses on wafer level only



## Background Info

- Cobra probe (5 mil diameter - flat tipped) is the primary contacting system for C4 VLSI test
- C4 = Controlled Collapse Chip Connection (Solder Bumps)
- C4's are normally reflowed before and after test
- Tests temperatures -10, 25, 85 and 100C
- Thermal unit range is -10 - 140C probe space transformer limit 100C (self imposed)



## Focus areas

- **Baseline comparison measurements to Lead Tin**
  - **Contact Resistance**
  - **Cleaning**
  - **Material Transfer (Pickup) To Probe Tip**
  - **Pad Deformation**
  - **Alignment to C4's (Solder Bumps)**

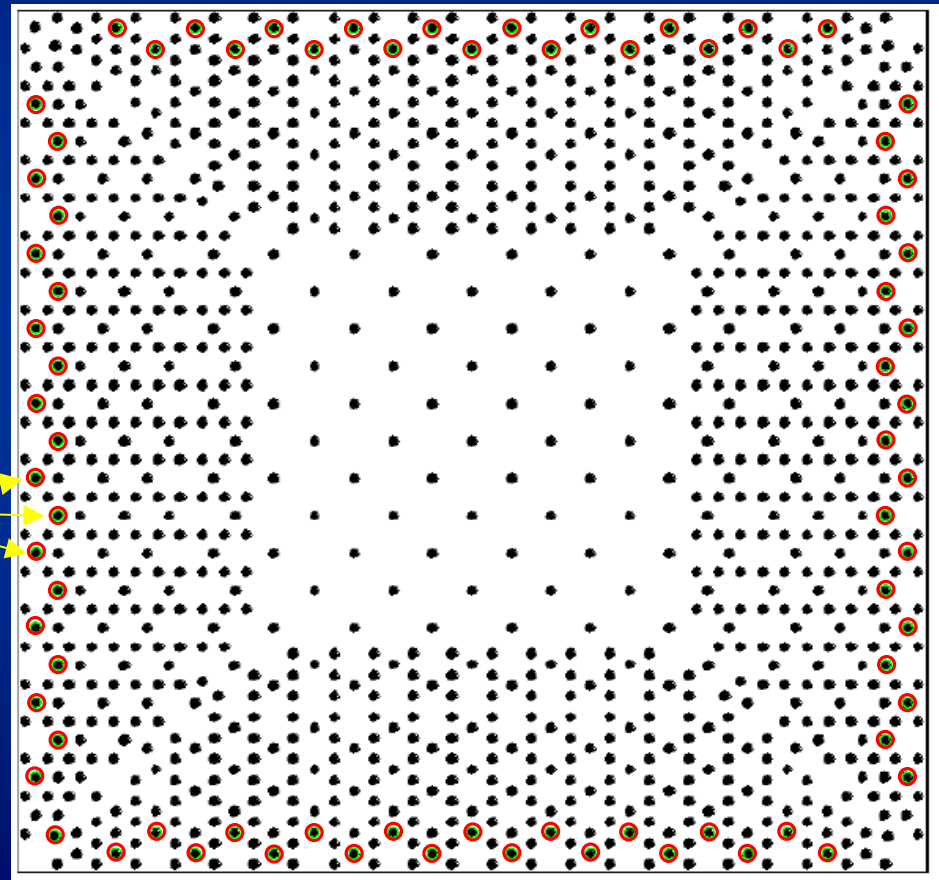


# Probe layout

76 contacts total

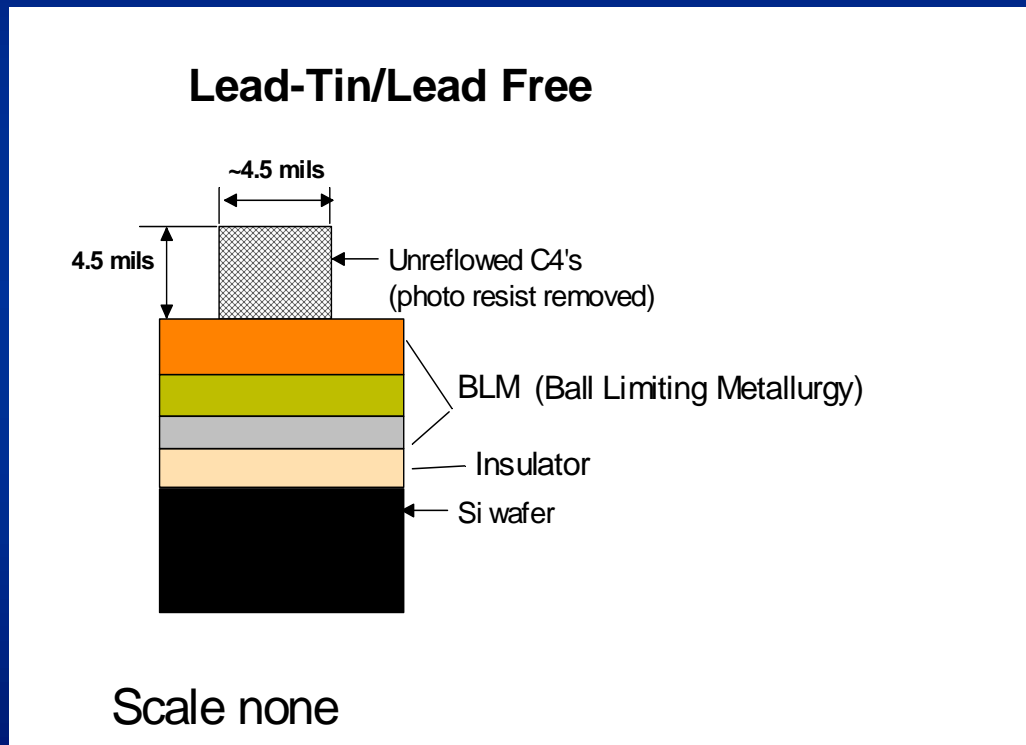
Die size ~ 9.1 mm square

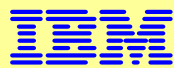
Probed pads





# Test wafer build structure





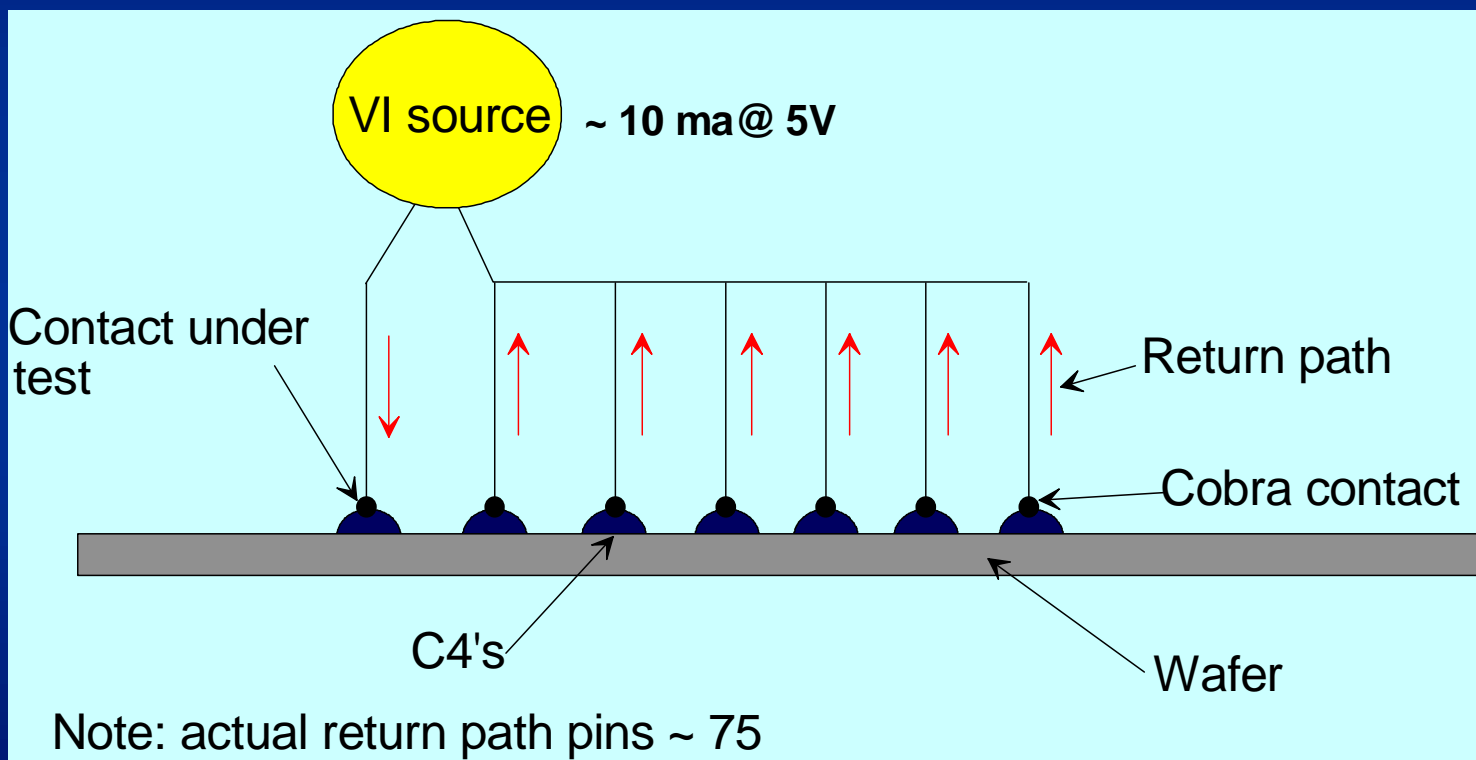
# Setup

- TEL P8XL wafer probing system with integral -10 to 140C thermal unit w/ IBM custom tester interface with hand wired space transformer
- Z drive - maximum impact velocity (~40 mm/sec)
- SARA (Socket Analog Resistance Analyzer) (DC switching matrix with measurement unit)
- Cres Measurement method - "pin return" with 10 ma forcing current and 5V clamp w/nulling file - to subtract path resistance
- Cleaning frequency - 1/wafer (>300 sites) - 5 micron abrasive material
- Environment - mini-clean hood over prober



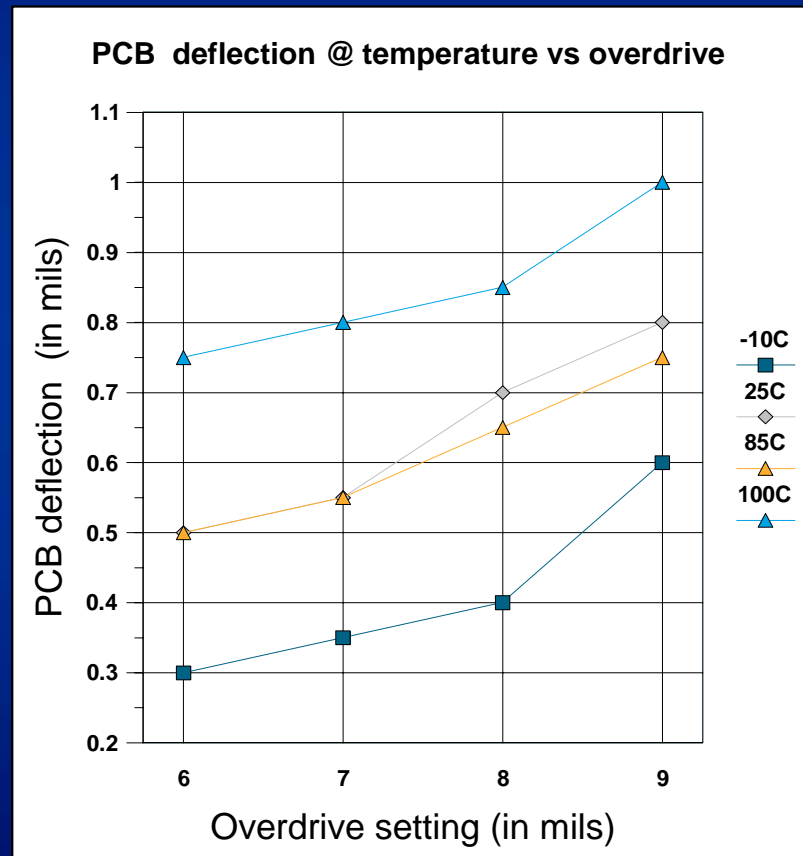
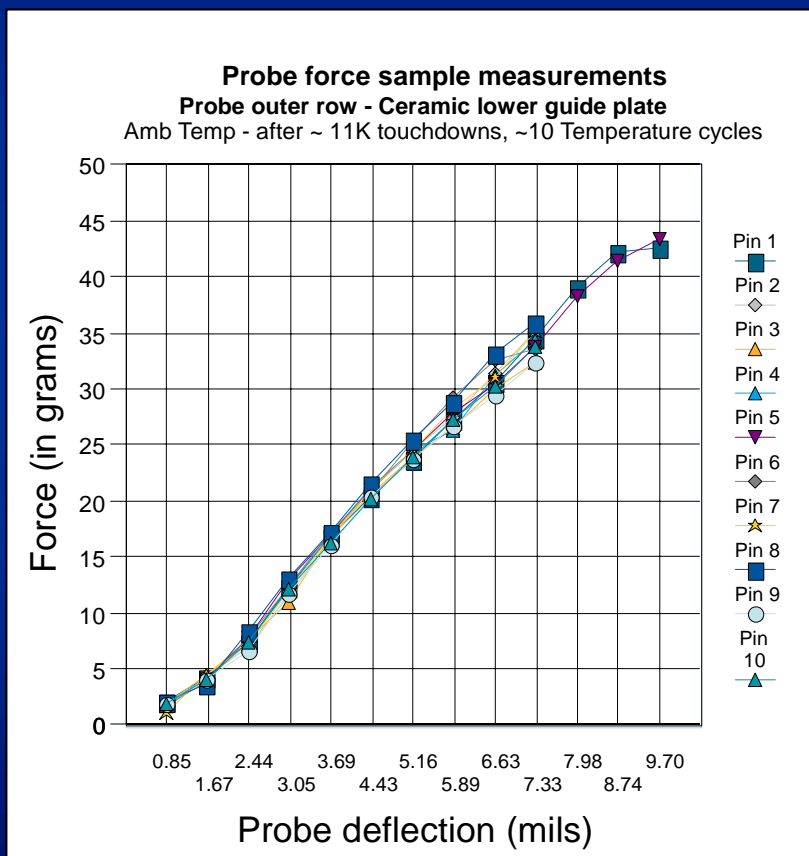


# Contact Resistance Measurement





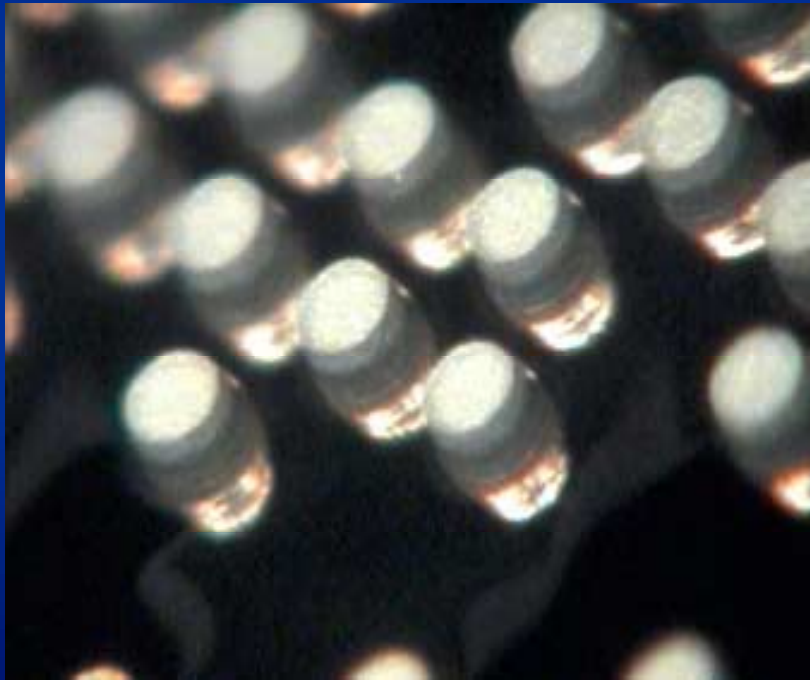
# Cobra Probe Measurements



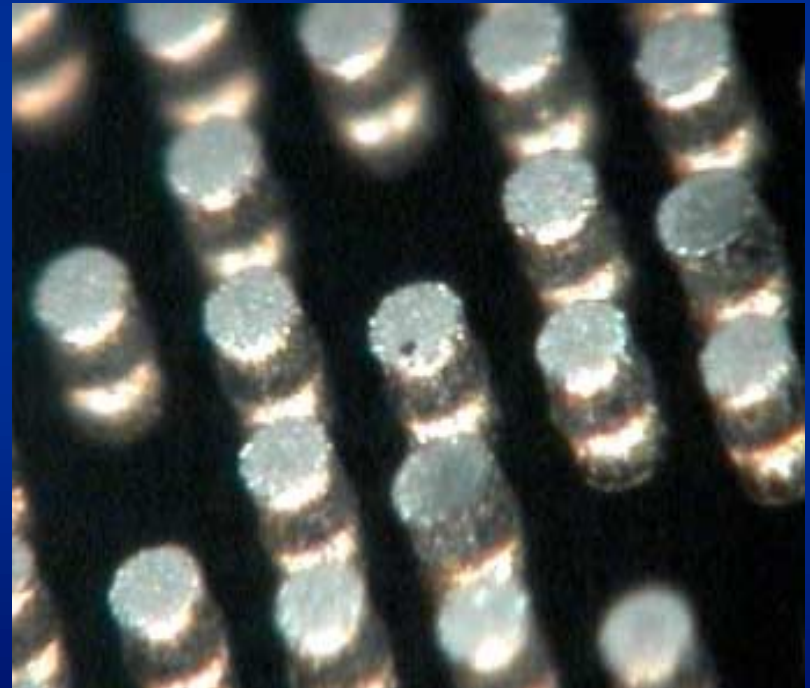


# Un Reflowed C4's

Lead free

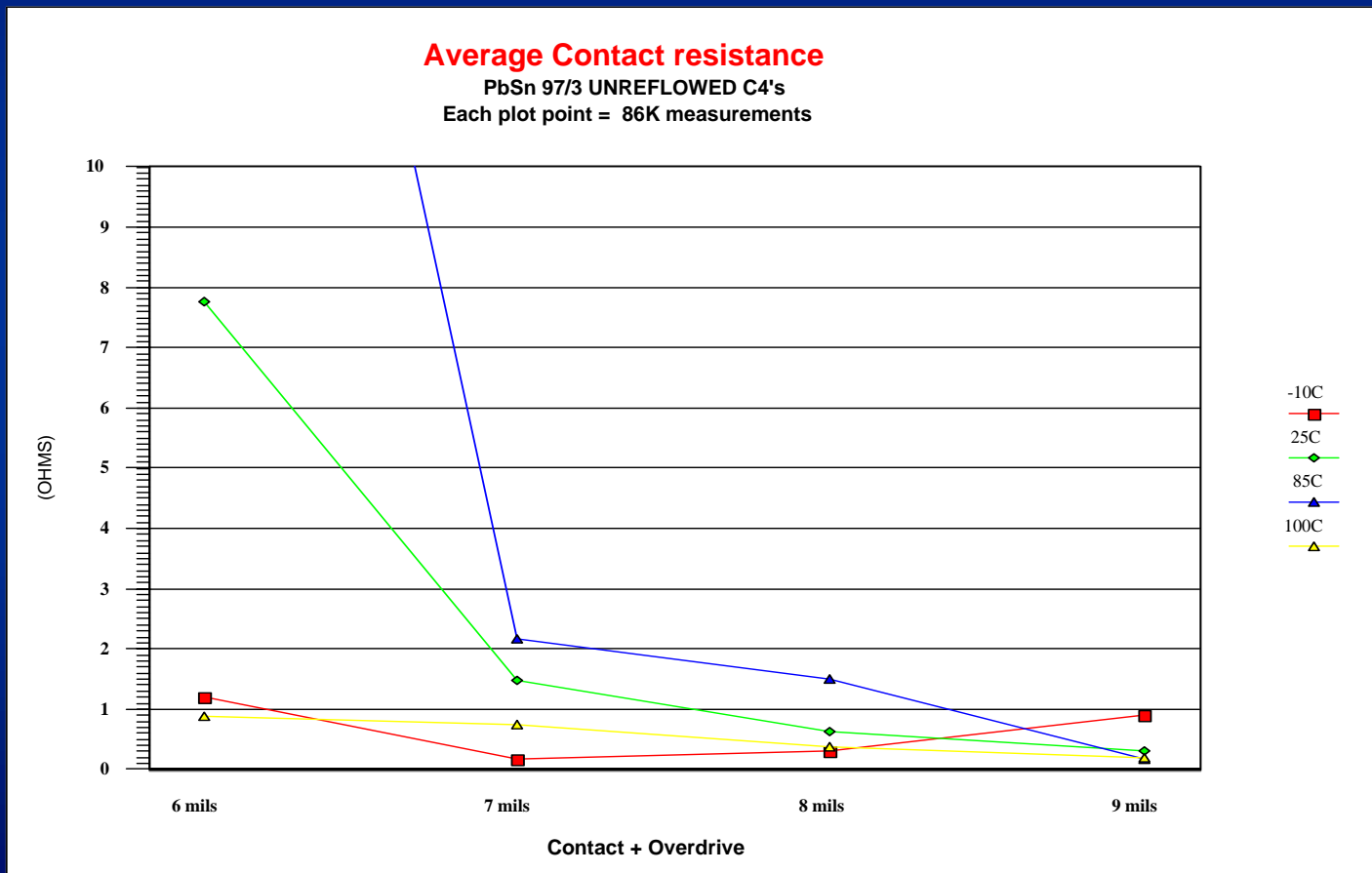


Lead Tin



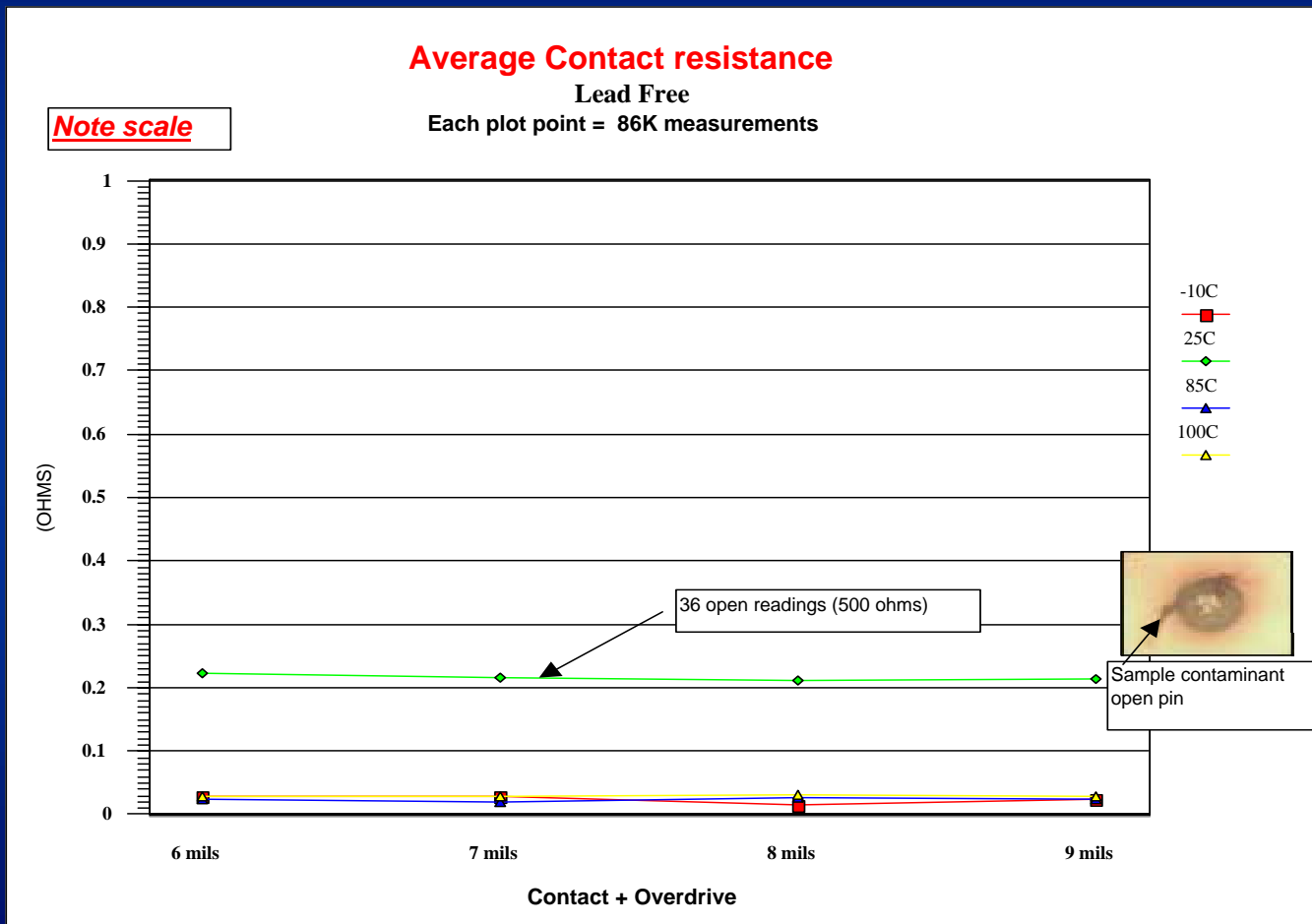


# Contact Resistance – Lead Tin C4's



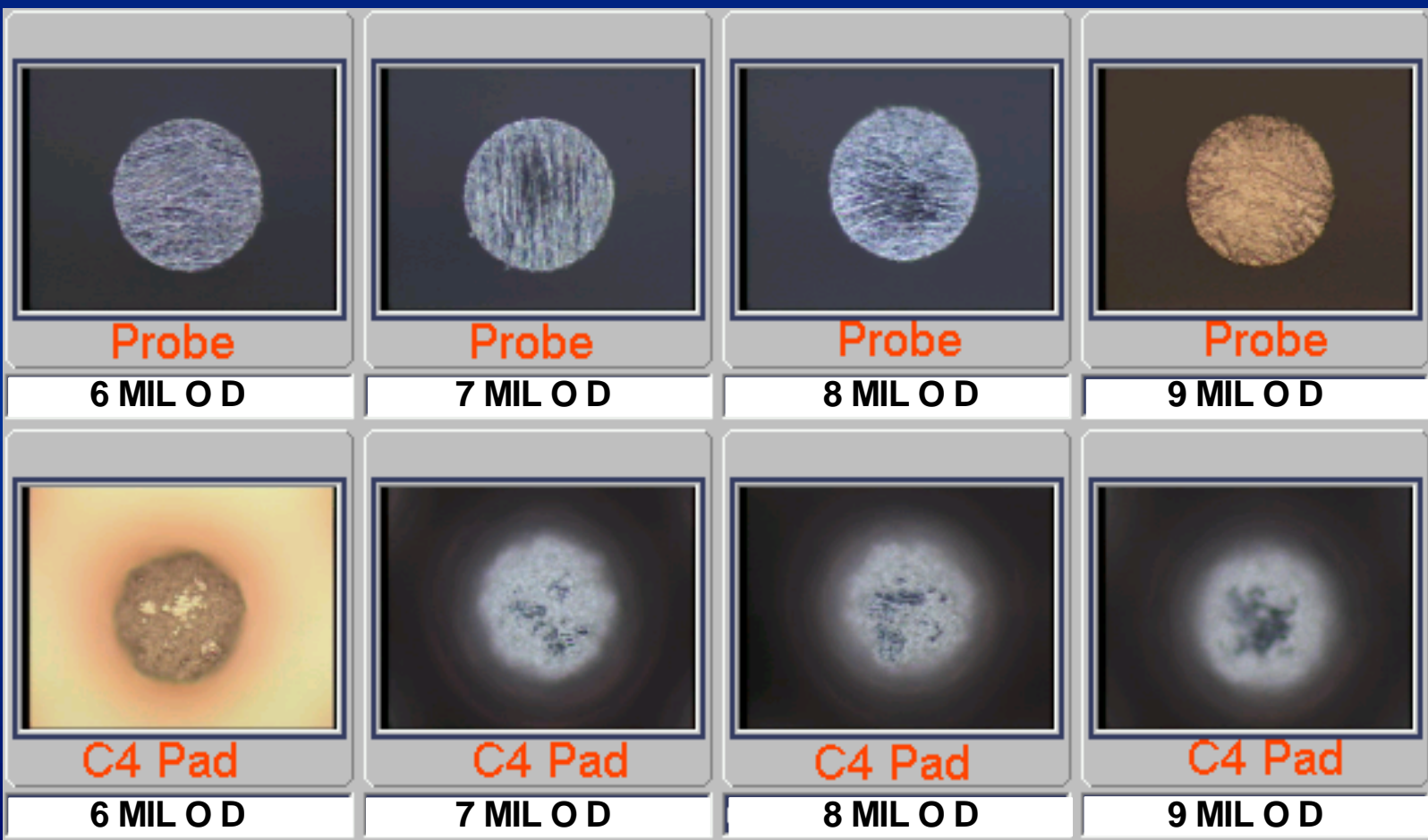


# Contact Resistance - Lead Free C4's



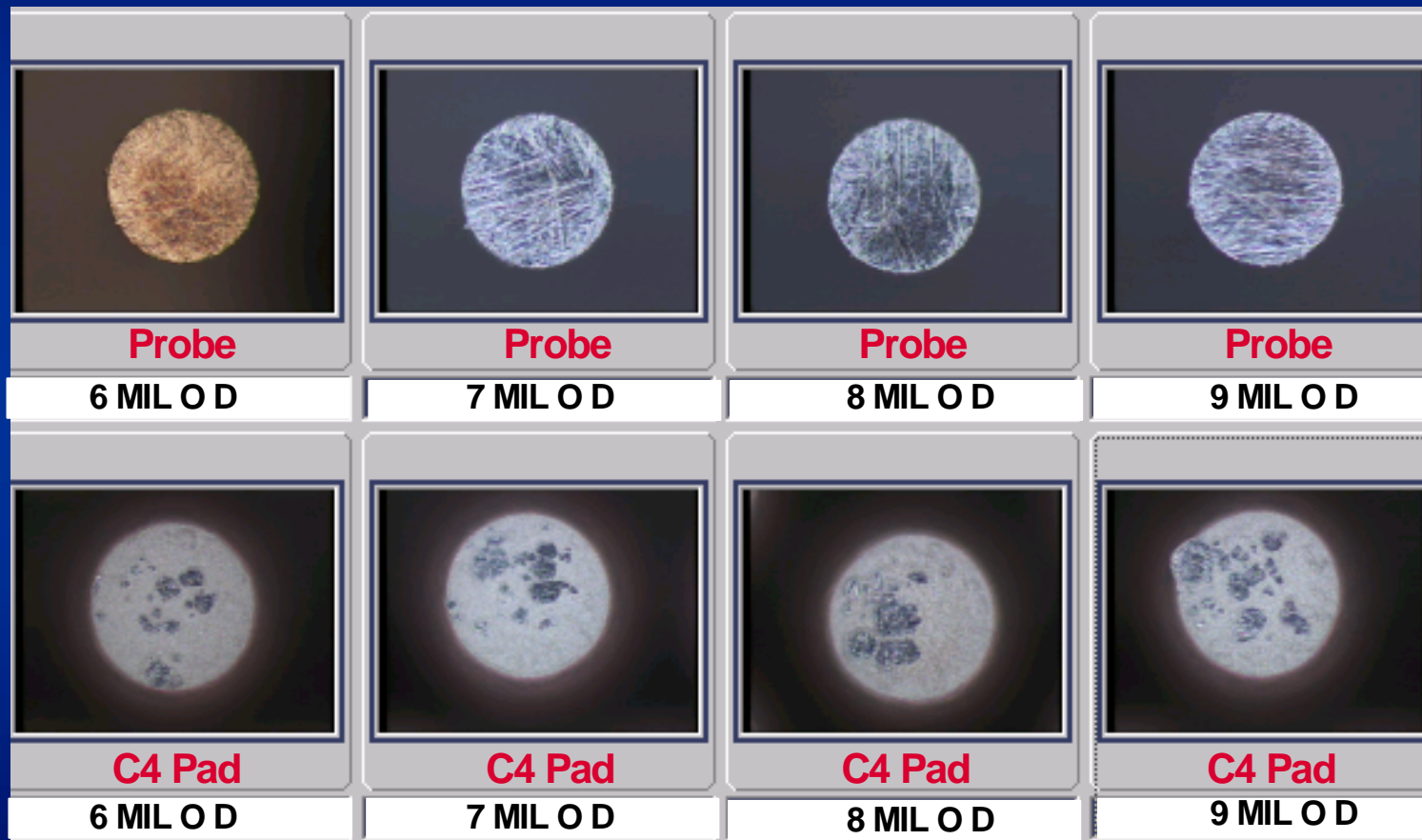


# -10°C Cobra/C4 Photos



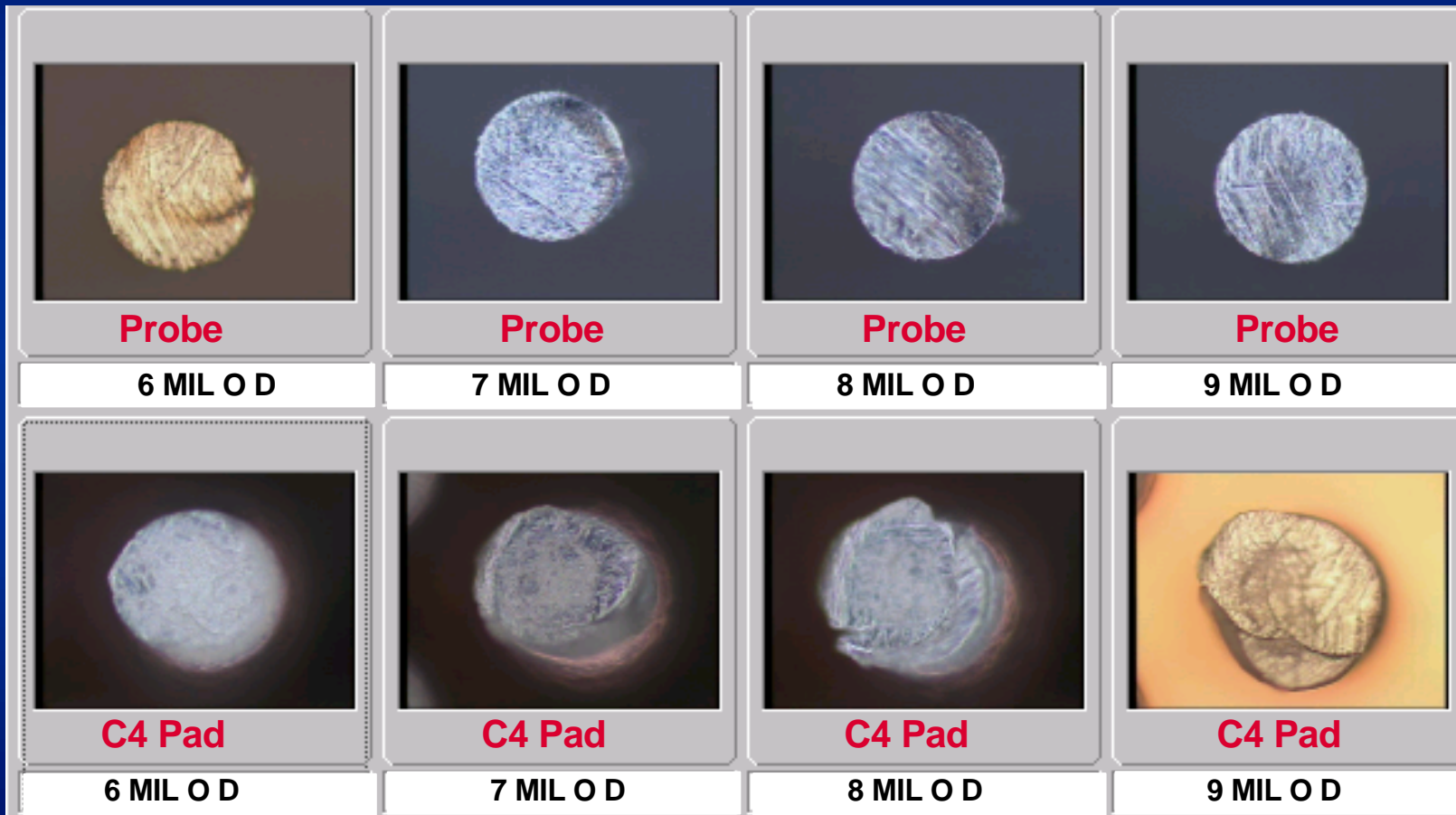


# 25°C Cobra/C4 Photos





# 85° C Cobra/C4 Photo's





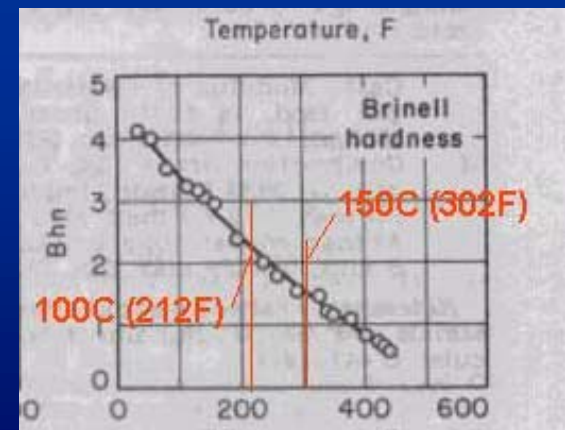
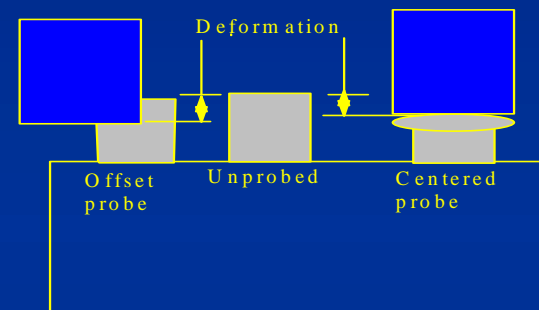
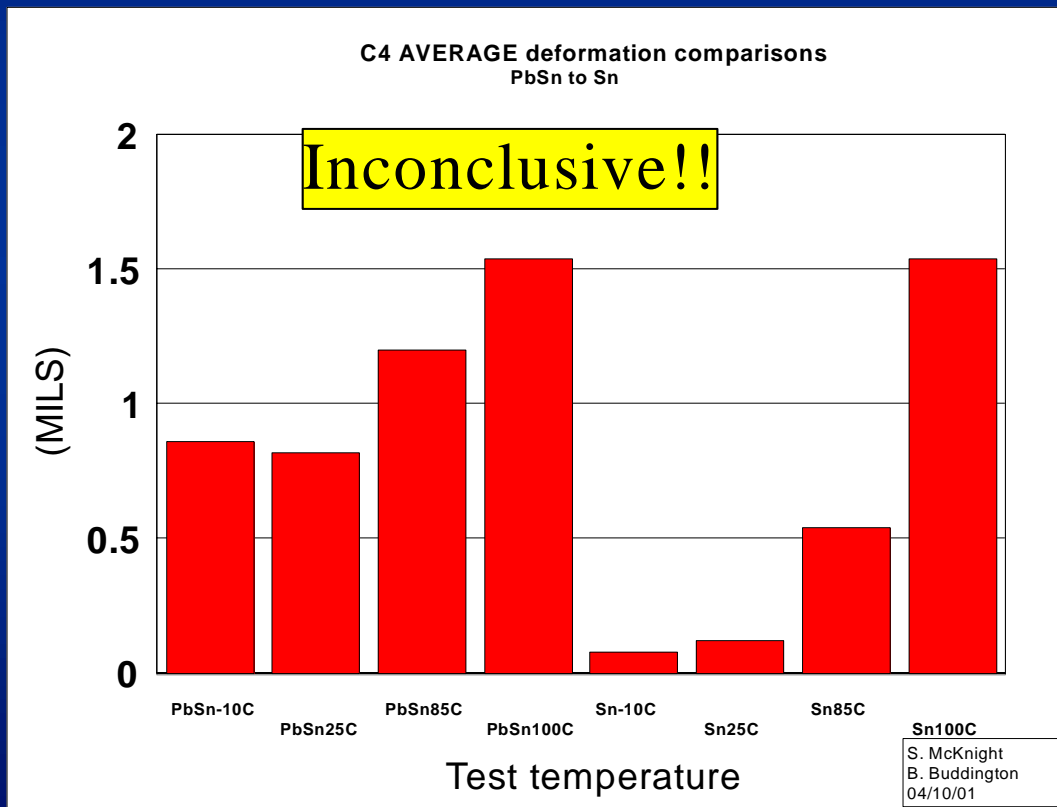


# 100°C Cobra/C4 Photo's





# Pad Deformation

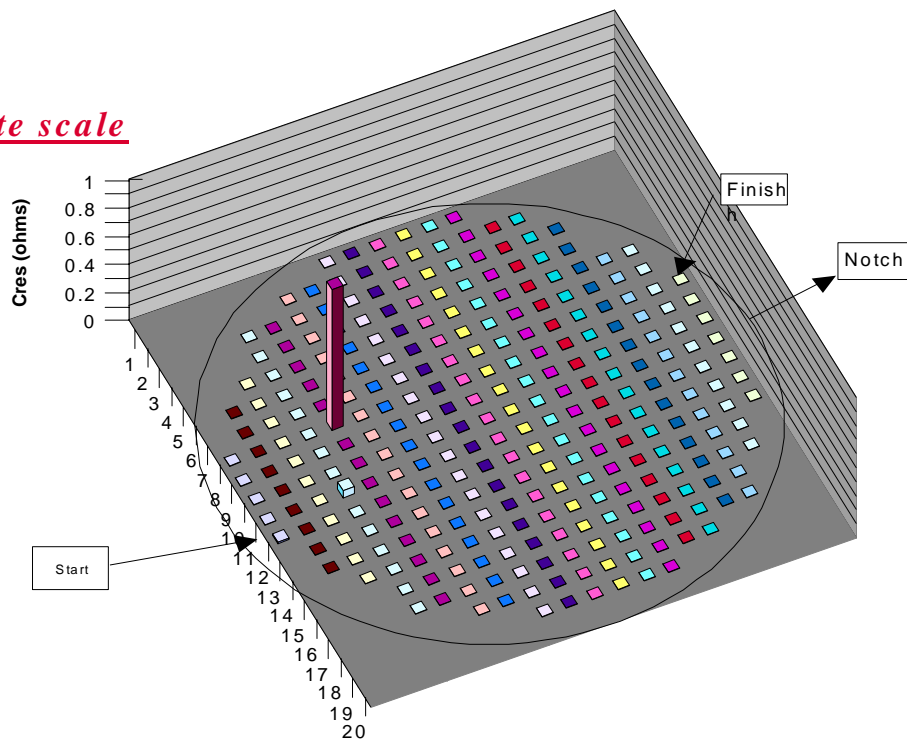




# Typical Wafer level Contact Resistance plot Lead Free C4's

Sn Average Contact Resistance/site  
6 mil OD - temperature -10C - 2nd pass  
283 sites/wafer

Note scale



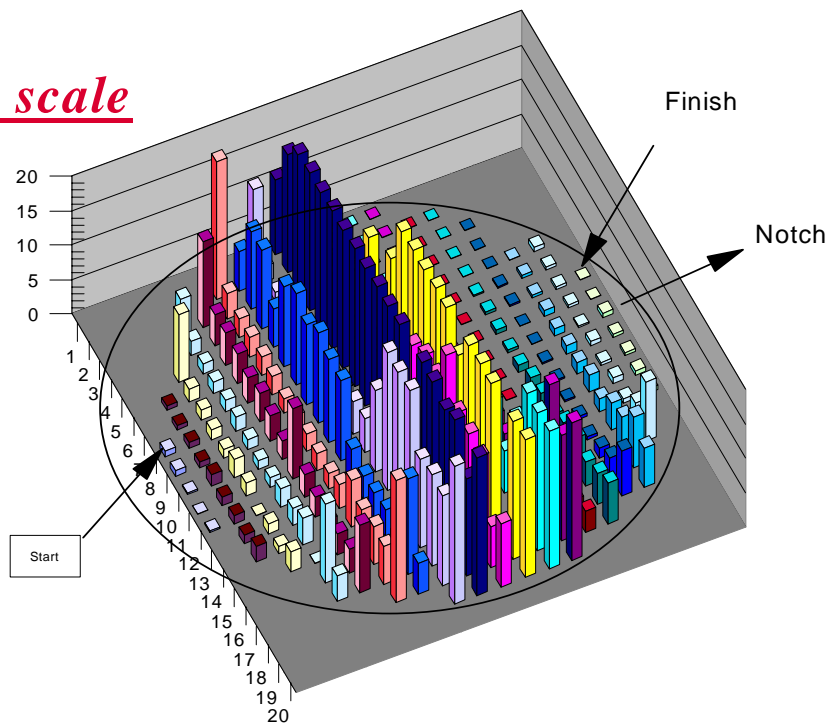
S. McKnight  
B. Buddington  
04/04/01



# Typical Wafer level Contact Resistance plot for Lead/Tin C4's

PbSn Baseline Average Contact Resistance/site  
6 milOD - temperature -  
25C 283 sites/wafer

Note scale



S. McKnight  
B. Buddington  
03/29/01



# Summary

- **Contact resistance for Lead Free  $\ll$  1-2 Ohms (temperature independent)**
- **Pad deformation – inconclusive – not an issue for post reflow operation**
- **Prober issues - auto alignment (non production wafers) Partial radius on top of pad not an issue**
- **Cleaning frequency, 1/wafer (~300+Die) is anticipated using standard (abrasive) cleaning materials**
- **Material transfer to probe tip comparable to Lead/Tin**



# Acknowledgements

**Barry Buddington – IBM - software/setup operations**

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